

LM98714

Three Channel, 16-Bit, 45 MSPS Digital Copier Analog Front End with Integrated CCD/CIS Sensor Timing **Generator and LVDS Output**

General Description

The LM98714 is a fully integrated, high performance 16-Bit, 45 MSPS signal processing solution for digital color copiers, scanners, and other image processing applications. Highspeed signal throughput is achieved with an innovative architecture utilizing Correlated Double Sampling (CDS), typically employed with CCD arrays, or Sample and Hold (S/H) inputs (for Contact Image Sensors and CMOS image sensors). The signal paths utilize 8 bit Programmable Gain Amplifiers (PGA), a +/-9-Bit offset correction DAC and independently controlled Digital Black Level correction loops for each input. The PGA and offset DAC are programmed independently allowing unique values of gain and offset for each of the three inputs. The signals are then routed to a 45MHz high performance analog-to-digital converter (ADC). The fully differential processing channel shows exceptional noise immunity, having a very low noise floor of -74dB. The 16-bit ADC has excellent dynamic performance making the LM98714 transparent in the image reproduction chain.

- Multi-Function Peripherals
- Facsimile Equipment
- Flatbed or Handheld Color Scanners
- High-speed Document Scanner

Applications

- Independent Gain/Offset Correction for Each Channel
- Digital Black Level Correction Loop for Each Channel
- Programmable Input Clamp Voltage
- Flexible CCD/CIS Sensor Timing Generator

Key Specifications

■ Maximum Input Level 1.2 or 2.4 Volt Modes

(both with + or - polarity option) ■ ADC Resolution 16-Bit

45 MSPS ADC Sampling Rate

+/- 23 LSB (typ)

 Channel Sampling Rate 15/22.5/30 MSPS ■ PGA Gain Steps 256 Steps

■ PGA Gain Range 0.7 to 7.84x Analog DAC Resolution +/-9 Bits

Analog DAC Range +/-300mV or +/-600mV

■ Digital DAC Resolution +/-6 Bits

-1024 LSB to + 1008 LSB Digital DAC Range -74dB (@0dB PGA Gain)

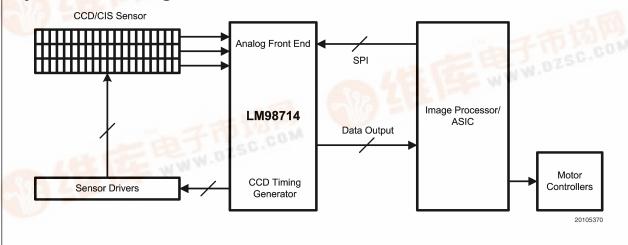
505mW (LVDS) 610mW (CMOS) Power Dissipation 0 to 70°C Operating Temp

Supply Voltage 3.3V Nominal (3.0V to 3.6V range)

Features

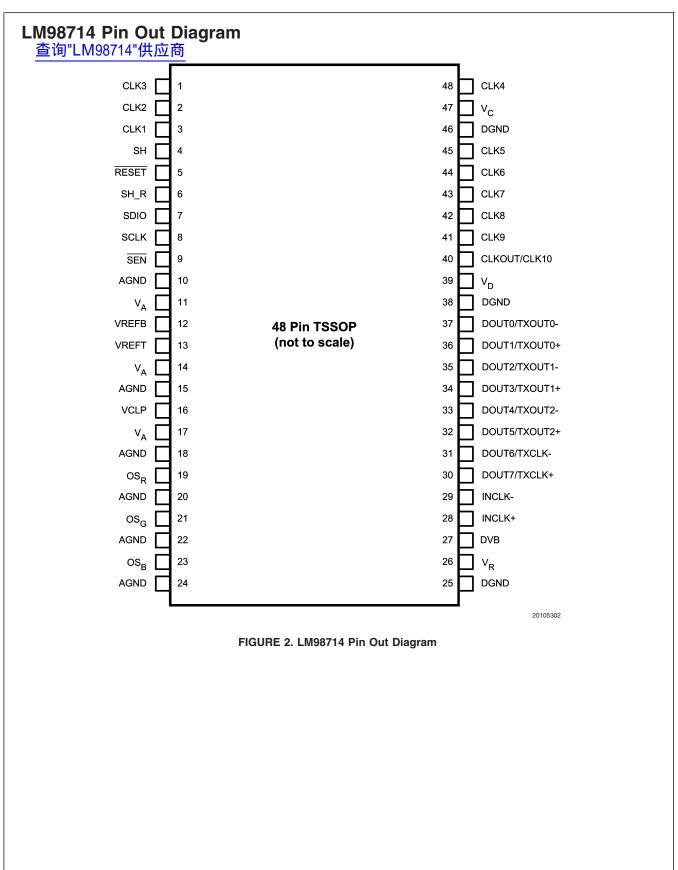
- LVDS/CMOS Outputs
- LVDS/CMOS Pixel Rate Input Clock or ADC Input Clock
- CDS or S/H Processing for CCD or CIS sensors

System Block Diagram



LM98714 Overall Chip Block Diagram 询"LM98714"供应商 DOUT5/ TXOUT2+ DOUT1/ TXOUT0+ DOUT4/ TXOUT2-DOUT3/ TXOUT1+ DOUT2/ TXOUT1-DOUT0/ TXOUT0-INCLK+ DOUT7/ TXCLK+ DOUT6/ TXCLK-INCLK-SCLK SDIO Data Out Config (CMOS/LVDS) Blue Ch Black Level Correction Serial Interface CLKOUT/ CLK10 Green Ch Black Level Correction CLK9 16 CLK8 Config Registers \oplus CCD Timing Generator CLK7 CLK6 Red Ch Black Level Correction CLK5 Bit ADC Digital Offset CLK4 CLK3 9 DGND DVB CLK2 CLK1 SH 3:1 NUX >8 SH_R ς VREFT PGA PGA 5:1 MUX PGA Reference Generator COLOR3PGA[7:0] COLOR4PGA[7:0] = COLOR5PGA[7:0] = COLOR2PGA[7:0] -COLOR2PGA[7:0] COLOR1PGA[7:0] COLOR3PGA[7:0] VREFB **▶**⊕ **▶**⊕ AGND VCLP Reference DAC Black Level Offset DAC Black Level Offset DAC Black Level Offset DAC CDS or Sample/Hold Amplifier or Sample/Hold Amplifier Sample/Hold Amplifier CDS CDS 5:1 MUX VCLP Reference Configuration COLOR4DAC[9:0] -COLOR3DAC[9:0] COLOR2DAC[9:0] COLOR2DAC[9:0] COLOR1DAC[9:0] COLOR3DAC[9:0] Input Bias/ Clamping Input Bias/ Clamping Input Bias/ Clamping VCLP os_G os_R os_B 20105301 FIGURE 1. Chip Block Diagram

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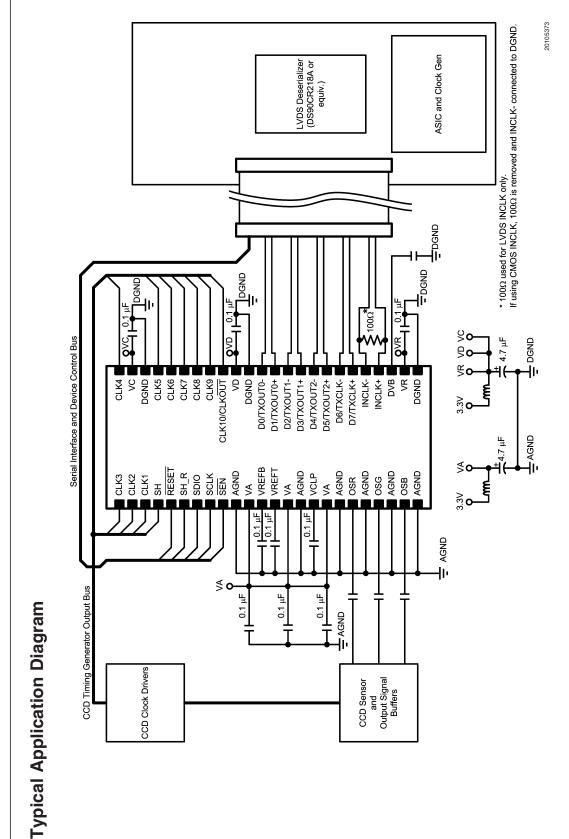


FIGURE 3. Typical Application Diagram

Pin Descriptions

Pin	7"L M98714'	170	Тур	Res	Description
1	CLK3	0	D	PU	Configurable sensor control output.
2	CLK2	0	D	PD	Configurable sensor control output.
3	CLK1	0	D	PU	Configurable sensor control output.
4	SH	0	D	PD	Sensor - Shift or transfer control signal for CCD and CIS sensors.
5	RESET	I	D	PU	Active-low master reset. NC when function not being used.
6	SH_R	I	D	PD	External request for an SH pulse.
7	SDIO	I/O	D		Serial Interface Data Input
8	SCLK	ı	D	PD	Serial Interface shift register clock.
9	SEN	ı	D	PU	Active-low chip enable for the Serial Interface.
10	AGND		Р		Analog ground return.
11	V _A		Р		Analog power supply. Bypass voltage source with 4.7μF and pin with 0.1μF to AGND.
12	VREFB	0	Α		Bottom of ADC reference. Bypass with a 0.1µF capacitor to ground.
13	VREFT	0	Α		Top of ADC reference. Bypass with a 0.1µF capacitor to ground.
14	V _A		Р		Analog power supply. Bypass voltage source with 4.7μF and pin with 0.1μF to AGND.
15	AGND		Р		Analog ground return.
16	VCLP	Ю	А		Input Clamp Voltage. Normally bypassed with a $0.1\mu F$, and a $4.7\mu F$ capacitor to AGND. An external reference voltage may be applied to this pin.
17	V _A		Р		Analog power supply. Bypass voltage source with $4.7\mu F$ and pin with $0.1\mu F$ to AGND.
18	AGND		Р		Analog ground return.
19	OS _R	I	Α		Analog input signal. Typically sensor Red output AC-coupled thru a capacitor.
20	AGND		Р		Analog ground return.
21	OS _G	I	Α		Analog input signal. Typically sensor Green output AC-coupled thru a capacitor.
22	AGND		Р		Analog ground return.
23	OS _B	I	Α		Analog input signal. Typically sensor Blue output AC-coupled thru a capacitor.
24	AGND		Р		Analog ground return.
25	DGND		Р		Digital ground return.
26	V _R		Р		Power supply input for internal voltage reference generator. Bypass this supply pin with a $0.1\mu F$ capacitor.
27	DVB	0	Р		Digital Core Voltage bypass. Not an input. Bypass with 0.1µF capacitor to DGND.
28	INCLK+	I	D		Clock Input. Non-Inverting input for LVDS clocks or CMOS clock input. CMOS clock is selected when pin 29 is held at DGND, otherwise clock is configured for LVDS operation.
29	INCLK-	I	D		Clock Input. Inverting input for LVDS clocks, connect to DGND for CMOS clock.
30	DOUT7/ TXCLK+	0	D		Bit 7 of the digital video output bus in CMOS Mode, LVDS Frame Clock+ in LVDS Mode.
31	DOUT6/ TXCLK-	0	D		Bit 6 of the digital video output bus in CMOS Mode, LVDS Frame Clock- in LVDS Mode.
32	DOUT5/ TXOUT2+	0	D		Bit 5 of the digital video output bus in CMOS Mode, LVDS Data Out2+ in LVDS Mode.
33	DOUT4/ TXOUT2-	0	D		Bit 4 of the digital video output bus in CMOS Mode, LVDS Data Out2- in LVDS Mode.
34	DOUT3/ TXOUT1+	0	D		Bit 3 of the digital video output bus in CMOS Mode, LVDS Data Out1+ in LVDS Mode.
35	DOUT2/ TXOUT1-	0	D		Bit 2 of the digital video output bus in CMOS Mode, LVDS Data Out1- in LVDS Mode.

Pin Descriptions (Continued) 词"LM98714"供应商

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Pin	Name	I/O	Тур	Res	Description
36	DOUT1/	0	D		Bit 1 of the digital video output bus in CMOS Mode, LVDS Data Out0+ in LVDS
	TXOUT0+				Mode.
37	DOUT0/	0	D		Bit 0 of the digital video output bus in CMOS Mode, LVDS Data Out0- in LVDS
	TXOUT0-				Mode.
38	DGND		Р		Digital ground return.
39	V _D		Р		Power supply for the digital circuits. Bypass this supply pin with 0.1µF
					capacitor. A single 4.7µF capacitor should be used between the supply and the
					VD, VR and VC pins.
40	CLKOUT/	0	D	PD	Output clock for registering output data when using CMOS outputs, or
	CLK10				configurable sensor control output.
41	CLK9	0	D	PD	Configurable sensor control output.
42	CLK8	0	D	PD	Configurable sensor control output.
43	CLK7	0	D	PD	Configurable sensor control output.
44	CLK6	0	D	PU	Configurable sensor control output.
45	CLK5	0	D	PD	Configurable sensor control output.
46	DGND		Р		Digital ground return.
47	V _C		Р		Power supply for the sensor control outputs. Bypass this supply pin with 0.1µF
					capacitor.
48	CLK4	0	D	PD	Configurable sensor control output.

(I=Input), (O=Output), (IO=Bi-directional), (P=Power), (D=Digital), (A=Analog), (PU=Pull Up with an internal resistor), (PD=Pull Down with an internal resistor.).

Absolute Maximum Ratings (Notes 2,

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If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Supply Voltage (VA,VR,VD,VC)	4.2V
Voltage on Any Input Pin	-0.3V to
(Not to exceed 4.2V)	(VA + 0.3V)
Voltage on Any Output Pin	-0.3V to
(execpt DVB and not to exceed	(VA + 0.3V)
4.2V)	
DVB Output Pin Voltage	2.0V

DVB Output Pin Voltage 2.0V
Input Current at any pin other than ±25 mA

Supply Pins (Note 3)

Package Input Current (except ±50 mA

Supply Pins) (Note 3)

Maximum Junction Temperature (TA) 150°C

Thermal Resistance (θ_{JA}) 66°C/W Package Dissipation at $T_A = 25$ °C 1.89W (Note 4)

ESD Rating (Note 5)

Human Body Model 2500V

Machine Model 250V

Storage Temperature -65°C to +150°C

Soldering process must comply with National

Semiconductor's Reflow Temperature Profile specifications. Refer to www.national.com/packaging. (Note 6)

Operating Ratings (Notes 1, 2)

Operating Temperature Range $0^{\circ}\text{C} \le \text{T}_{\text{A}} \le +70^{\circ}\text{C}$ All Supply Voltage +3.0V to +3.6V

Electrical Characteristics

The following specifications apply for VA = VD = VR = VC = 3.3V, C_L = 10pF, and f_{INCLK} = 15MHz unless otherwise specified. Boldface limits apply for T_A = T_{MIN} to T_{MAX} ; all other limits T_A = 25°C.

Symbol	Parameter	Conditions	Min	Typ (Note 8)	Max	Units
	tal Input DC Specifications (RESE		IVIIII	(Note o)	IVICA	Onits
V _{IH}	Logical "1" Input Voltage		2.0			V
V _{IL}	Logical "0" Input Voltage				0.8	V
I _{IH}	Logical "1" Input Current	V _{IH} = VD				
		RESET		235		nA
		SH_R, SCLK		70		μΑ
		SEN		130		nA
I _{IL}	Logical "0" Input Current	VIL = DGND				
		RESET		70		μA
		SH_R, SCLK		235		nA
		SEN		70		μA
MOS Digit	tal Output DC Specifications (SH,	CLK1 to CLK10, CMOS Data C	outputs)			
V _{OH}	Logical "1" Output Voltage	I _{OUT} = -0.5mA	2.95			V
V _{OL}	Logical "0" Output Voltage	I _{OUT} = 1.6mA			0.25	V
Ios	Output Short Circuit Current	V _{OUT} = DGND		16		mA
		V _{OUT} = VD		-20		
l _{oz}	CMOS Output TRI-STATE	V _{OUT} = DGND		20		nA
	Current	$V_{OUT} = VD$		-25		
MOS Digit	tal Input/Output DC Specifications	(SDIO)				
I _{IH}	Logical "1" Input Current	V _{IH} = VD		90		nA
I _{IL}	Logical "0" Input Current	V _{IL} = DGND		90		nA
.VDS/CMO	S Clock Receiver DC Specificatio	ns (INCLK+ and INCLK- Pins)				
V _{IHL}	Differential LVDS Clock	R _L = 100W			100	mV
	High Threshold Voltage	V _{CM} (LVDS Input Common				
		Mode Voltage)= 1.25V				
V_{ILL}	Differential LVDS Clock		-100			mV
	Low Threshold Voltage					

20.0.00	limits apply for $T_A = T_{MIN}$ to T_{MAX}	all other limits T _A = 25°C.				
Symbol	Parameter	Conditions	Min	Typ (Note 8)	Max	Uni
V _{IHC}	CMOS Clock	INCLK- = DGND	2.0	,		V
	High Threshold Voltage					
V _{ILC}	CMOS Clock	1			0.8	V
	Low Threshold Voltage					
I _{IHL}	CMOS Clock				280	μΑ
	Input High Current					
I _{ILC}	CMOS Clock				-150	μA
.20	Input Low Current					
LVDS Outp	out DC Specifications					
V _{OD}	Differential Output Voltage	$R_L = 100\Omega$	180	328	450	m\
V _{os}	LVDS Output Offset Voltage	- 	1.17	1.23	1.3	V
I _{os}	Output Short Circuit Current	$V_{OUT} = 0V, R_L = 100\Omega$		7.9		m/
	pply Specifications			1		1
IA	VA Analog Supply Current	VA Normal State	60	97	125	m/
		VA Low Power State	12	23	32	m/
		(Powerdown)				
IR	VR Digital Supply Current	VR Normal State	30	64	75	m/
		(LVDS Outputs)				
		CMOS Output Data Format	15	47	55	m
		LVDS Output Data Format		47		m/
		with Data Outputs Disabled				
ID	VD Digital Output Driver Supply	LVDS Output Data Format		0.05		m/
	Current	CMOS Output Data Format	12		40	m/
		(ATE Loading of CMOS				
		Outputs > 50pF)				
IC	VC CCD Timing Generator	Typical sensor outputs:	0.5		12	m/
	Output Driver Supply Current	SH, CLK1=Φ1A, CLK2=Φ2A,				
		CLK3=ФВ, CLK4=ФС,				
		CLK5=RS, CLK6=CP				
		(ATE Loading of CMOS				
		Outputs > 50pF)				
PWR	Average Power Dissipation	LVDS Output Data Format	350	505	650	m۷
		CMOS Output Data Format	380	610	700	m۷
		(ATE Loading of CMOS				
		Outputs > 50pF)				
Input Sam	pling Circuit Specifications					
V_{IN}	Input Voltage Level	CDS Gain=1x, PGA Gain=1x		2.3		Vp
		CDS Gain=2x, PGA Gain=		1.22		
		1x				1

Electrical Characteristics (Continued)

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Symbol	Parameter	Conditions	Min	(Note 8)	Max	Units
I _{IN_SH}	Sample and Hold Mode	Source Followers Off	50		70	μΑ
	Input Leakage Current	CDS Gain = 1x	(-70)		(-40)	
		$OS_X = VA (OS_X = AGND)$				
		Source Followers Off	75		105	μΑ
		CDS Gain = 2x	(-105)		(-75)	
		$OS_X = VA (OS_X = AGND)$, ,	
		Source Followers On	-200	-10	200	nA
		CDS Gain = 2x		-16		
		$OS_X = VA (OS_X = AGND)$		10		
	Sample/Hold Mode	CDS Gain = 1x		2.5		nE
C_{SH}	· .	CDS Gaill = 1x		2.5		pF
	Equivalent Input Capacitance	00000				
	(see Figure 11)	CDS Gain = 2x		4		pF
I_{IN_CDS}	CDS Mode	Source Followers Off	-300	7	300	nA
	Input Leakage Current	$OS_X = VA (OS_X = AGND)$		(-25)		
R_{CLPIN}	CLPIN Switch Resistance			16	50	Ω
	(OS _x to VCLP Node in Figure 8)					
VCLP Refe	rence Circuit Specifications					
	VCLP DAC Resolution			4		Bits
	VCLP DAC Step Size			0.16		V
V _{VCLP}	VCLP DAC Voltage Min Output	VCLP Config. Register = 0001 0000b	0.14	0.26	0.43	V
	VCLP DAC Voltage Max Output	VCLP Config. Register = 0001 1111b	2.38	2.68	2.93	V
	Resistor Ladder Enabled		1.54	V / 0	1.73	V
	Resistor Lauder Eriabled	VCLP Config. Register = 0010 xxxxb	1.54	V _A / 2	1.73	V
I _{sc}	VCLP DAC Short Circuit Output	VCLP Config. Register =		30		mA
	Current	0001 xxxxb				
Black Leve	el Offset DAC Specifications					
	Resolution			10		Bits
	Monotonicity		G	uaranteed by	characterizat	
	Offset Adjustment Range	CDS Gain = 1x				
	Referred to AFE Input	Minimum DAC Code =		-614		
	Treferred to At E Input	0x000		-014		mV
		Maximum DAC Code =		614		1117
		0x3FF		014		
		CDS Gain = 2x				
				007		
		Minimum DAC Code =		-307		
		0x000		007		mV
		Maximum DAC Code = 0x3FF		307		
	Offset Adjustment Range	Minimum DAC Code =	-16000		-18200	
		0x000				1.00
	Referred to AFE Output	Maximum DAC Code = 0x3FF	16000		18200	LSB
	DAC LSB Stop Sizo	CDS Gain = 1x		1.2		mV
	DAC LSB Step Size					
	5	Referred to AFE Output	0.5-	(32)	0.5-	(LSB)
DNL	Differential Non-Linearity		-0.95		3.25	LSB

Electrical Characteristics (Continued)

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Symbol	Parameter	Conditions	Min	(Note 8)	Max	Units
INL	Integral Non-Linearity		-3.1		2.65	LSB
PGA Spec	ifications					•
	Gain Resolution			8		Bits
	Monotonicity		G	uaranteed by	characteriza	tion
	Maximum Gain	CDS Gain = 1x	7.18	7.9	8.77	V/V
		CDS Gain = 1x	17.1	17.9	18.9	dB
	Minimum Gain	CDS Gain = 1x	0.56	0.7	0.82	V/V
		CDS Gain = 1x	-5	-3	-1.72	dB
	PGA Function	Gain (V/\	/) = (196/(2	280-PGA Code	e))	
		,	, , ,	96/(280-PGA		
	Channel Matching	Minimum PGA Gain	`	3	,,	%
		Maximum PGA Gain		12.7		
ADC Spec	ifications			l		1
V _{REFT}	Top of Reference			2.07		V
V _{REFB}	Bottom of Reference			0.89		V
V _{REFT} -	Differential Reference Voltage		1.07	1.18	1.29	V
V _{REFB}						
	Overrange Output Code			65535		
	Underrange Output Code			0		
Digital Off	set "DAC" Specifications					
	Resolution			7		Bits
	Digital Offset DAC LSB Step Size	Referred to AFE Output		16		LSB
	Offset Adjustment Range	Min DAC Code =7b0000000		-1024		
	Referred to AFE Output	Mid DAC Code =7b1000000		0		LSB
		Max DAC Code =		1008		LOD
		7b1111111				
Full Chanr	nel Performance Specifications					
DNL	Differential Non-Linearity		-0.99	0.8/-0.6	2.55	LSB
INL	Integral Non-Linearity		-73	+/-23	78	LSB
SNR	Total Output Noise	Minimum PGA Gain		-79		dB
				7.2		LSB
						RMS
		PGA Gain = 1x		-74		dB
				13	30	LSB
						RMS
		Maximum PGA Gain		-56		dB
				104		LSB
						RMS
	Channel to Channel Crosstalk	Mode 3		47		LSB
		Mode 2		16		LOD

Note 1: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions, see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed. Some performance characteristics may degrade when the device is not operated under the listed test conditions. Operation of the device beyond the Operating Ratings is not recommended.

Note 2: All voltages are measured with respect to AGND = DGND = 0V, unless otherwise specified.

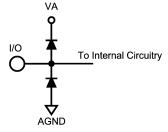
Note 3: When the input voltage (V_{IN}) at any pin exceeds the power supplies $(V_{IN} < GND \text{ or } V_{IN} > V_A \text{ or } V_D)$, the current at that pin should be limited to 25 mA. The 50 mA maximum package input current rating limits the number of pins that can simultaneously safely exceed the power supplies with an input current of 25 mA to two.

Note 4: The maximum power dissipation must be derated at elevated temperatures and is dictated by T_{JMAX} , θ_{JA} and the ambient temperature, T_A . The maximum allowable power dissipation at any temperature is $P_D = (T_{JMAX} - T_A)/\theta_{JA}$. The values for maximum power dissipation listed above will be reached only when the devices $T_{JMAX} = T_{JA}/\theta_{JA}$. The values for maximum power dissipation listed above will be reached only when the devices $T_{JMAX} = T_{JA}/\theta_{JA}$. The values for maximum power dissipation listed above will be reached only when the devices $T_{JMAX} = T_{JA}/\theta_{JA}$. The values for maximum power dissipation at any temperature, $T_{JA} = T_{JA}/\theta_{JA}$. The values for maximum power dissipation at any temperature, $T_{JA} = T_{JA}/\theta_{JA}$. The values for maximum power dissipation at any temperature, $T_{JA} = T_{JA}/\theta_{JA}$. The values for maximum power dissipation at any temperature, $T_{JA} = T_{JA}/\theta_{JA}$. The values for maximum power dissipation listed above will be reached only when the devices $T_{JA} = T_{JA}/\theta_{JA}$. The values for maximum power dissipation listed above will be reached only when the devices $T_{JA} = T_{JA}/\theta_{JA}$. The values for maximum power dissipation listed above will be reached only when the devices $T_{JA} = T_{JA}/\theta_{JA}$. The values for maximum power dissipation listed above will be reached only when the devices $T_{JA} = T_{JA}/\theta_{JA}$. The values for maximum power dissipation listed above will be reached only when the devices $T_{JA} = T_{JA}/\theta_{JA}$. The values for maximum power dissipation listed above will be reached only when the devices $T_{JA} = T_{JA}/\theta_{JA}$. The values $T_{JA} = T_{JA}/\theta_{JA}$ and $T_{JA} = T_{JA}/\theta_{JA}$. The values for maximum power dissipation listed above will be reached only when the devices $T_{JA} = T_{JA}/\theta_{JA}$. The values $T_{JA} = T_{JA}/\theta_{JA}$ and $T_{JA} = T_{JA}/\theta_{JA}$ and $T_{JA} = T_{JA}/\theta_{JA}$.

Note 5: Human body model is 100 pF capacitor discharged through a 1.5 k Ω resistor. Machine model is 220 pF discharged through 0Ω .

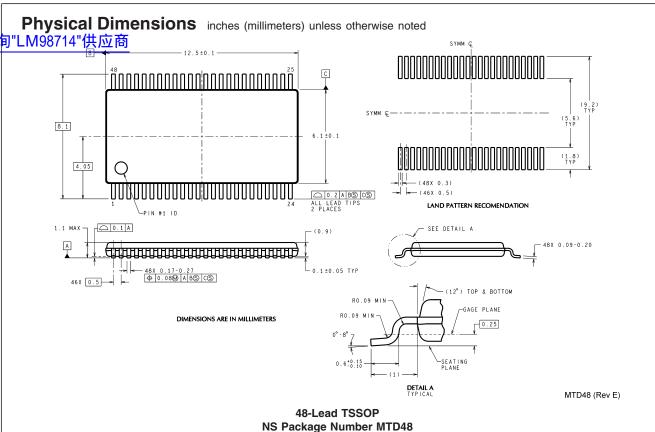
Note 6: Reflow temperature profiles are different for lead-free and non-lead-free packages.

Note 7: The analog inputs are protected as shown below. Input voltage magnitudes beyond the supply rails will not damage the device, provided the current is limited per note 3. However, input errors will be generated If the input goes above VA and below AGND.



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Note 8: Typical figures are at $T_A = 25$ °C, and represent most likely parametric norms at the time of product characterization. The typical specifications are not guaranteed.



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